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Liu et al.

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(54) **LATERAL MOSFET**

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H01L 29/78 (2006.01)
H01L 27/088 (2006.01)
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USPC 257/374, 510, 321
See application file for complete search history.

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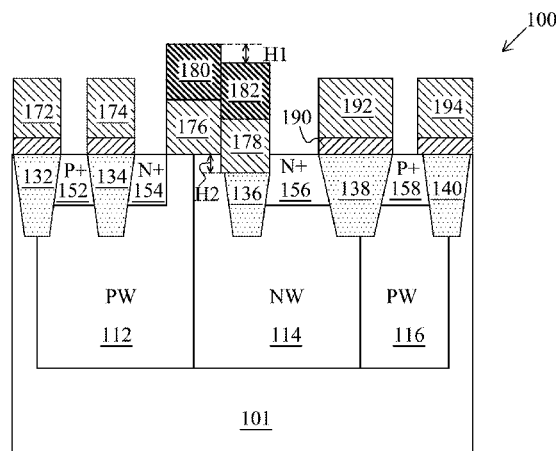
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(57) **ABSTRACT**

A lateral MOSFET comprises a plurality of isolation regions formed in a substrate, wherein a first isolation region is of a top surface lower than a top surface of the substrate. The lateral MOSFET further includes a gate electrode layer having a first gate electrode layer formed over the first isolation region and a second gate electrode layer formed over the top surface of the substrate, wherein a top surface of the first gate electrode layer is lower than a top surface of the second gate electrode layer.

20 Claims, 16 Drawing Sheets



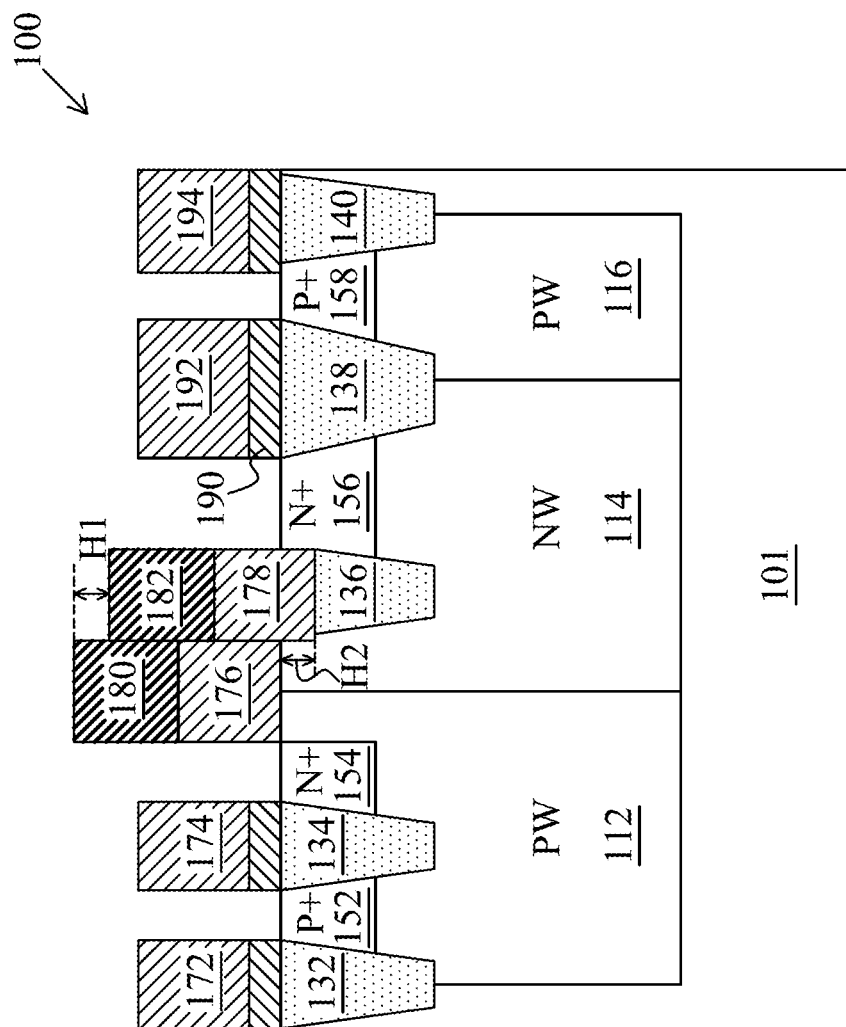
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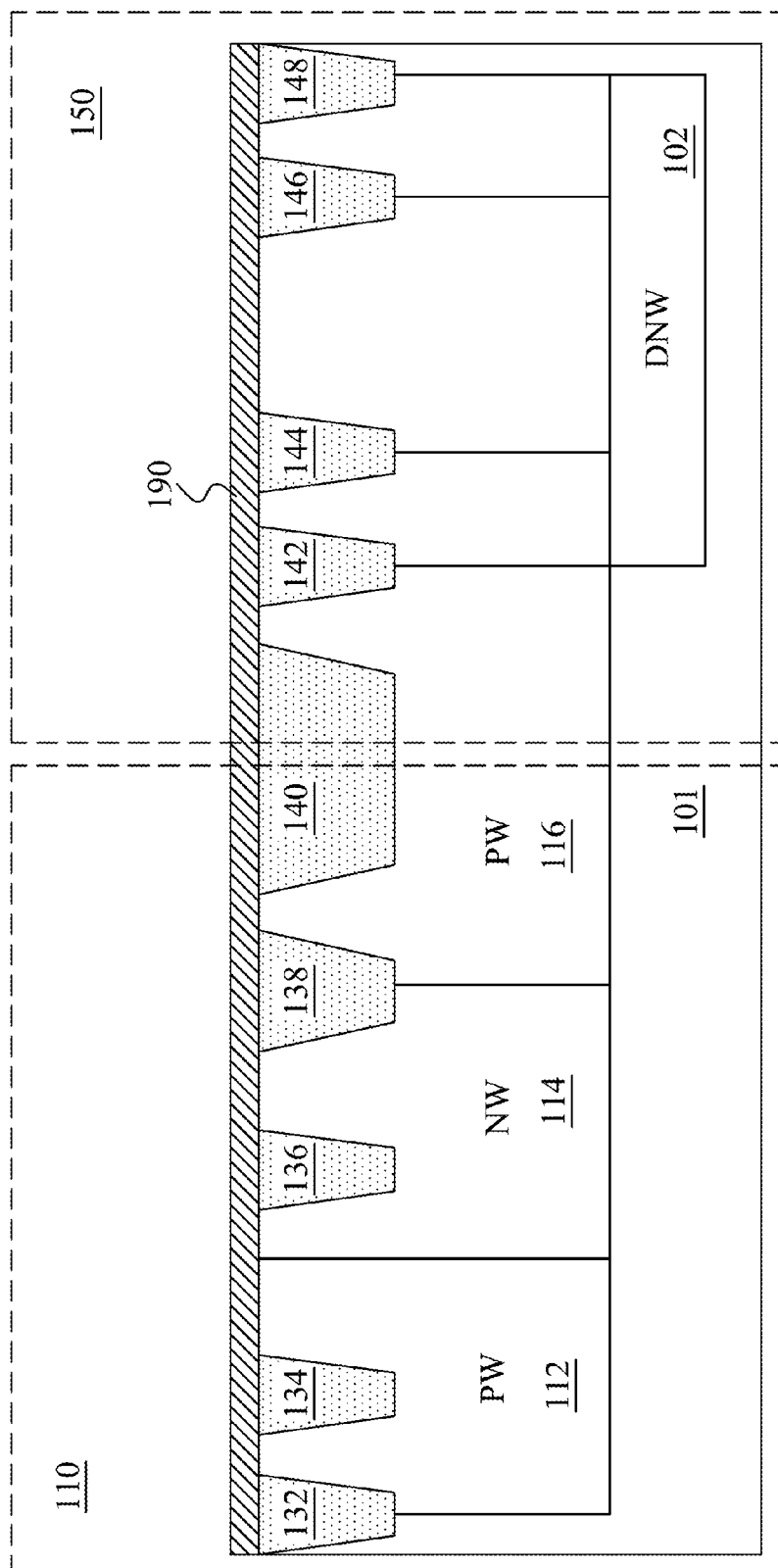


Fig. 2

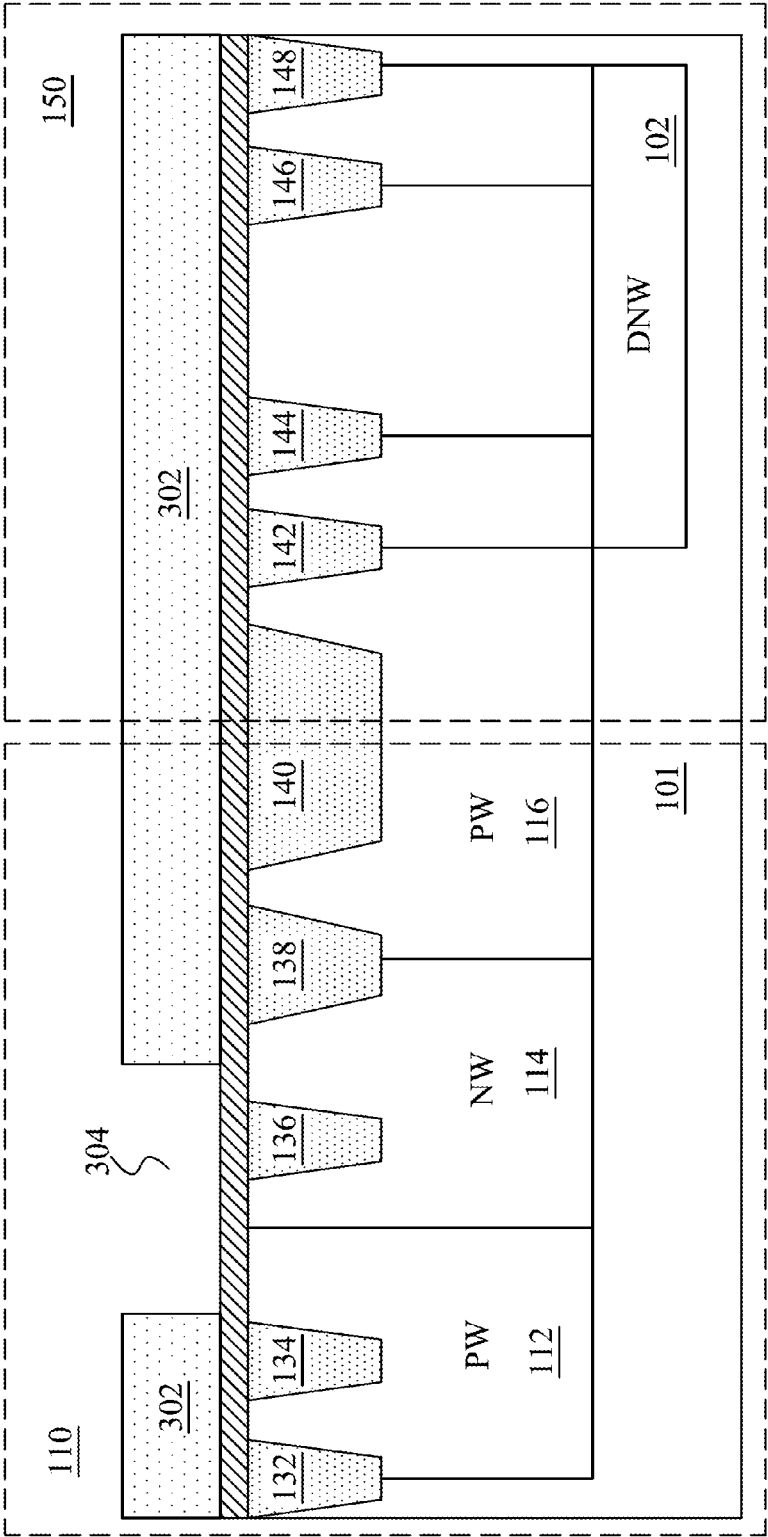


Fig. 3

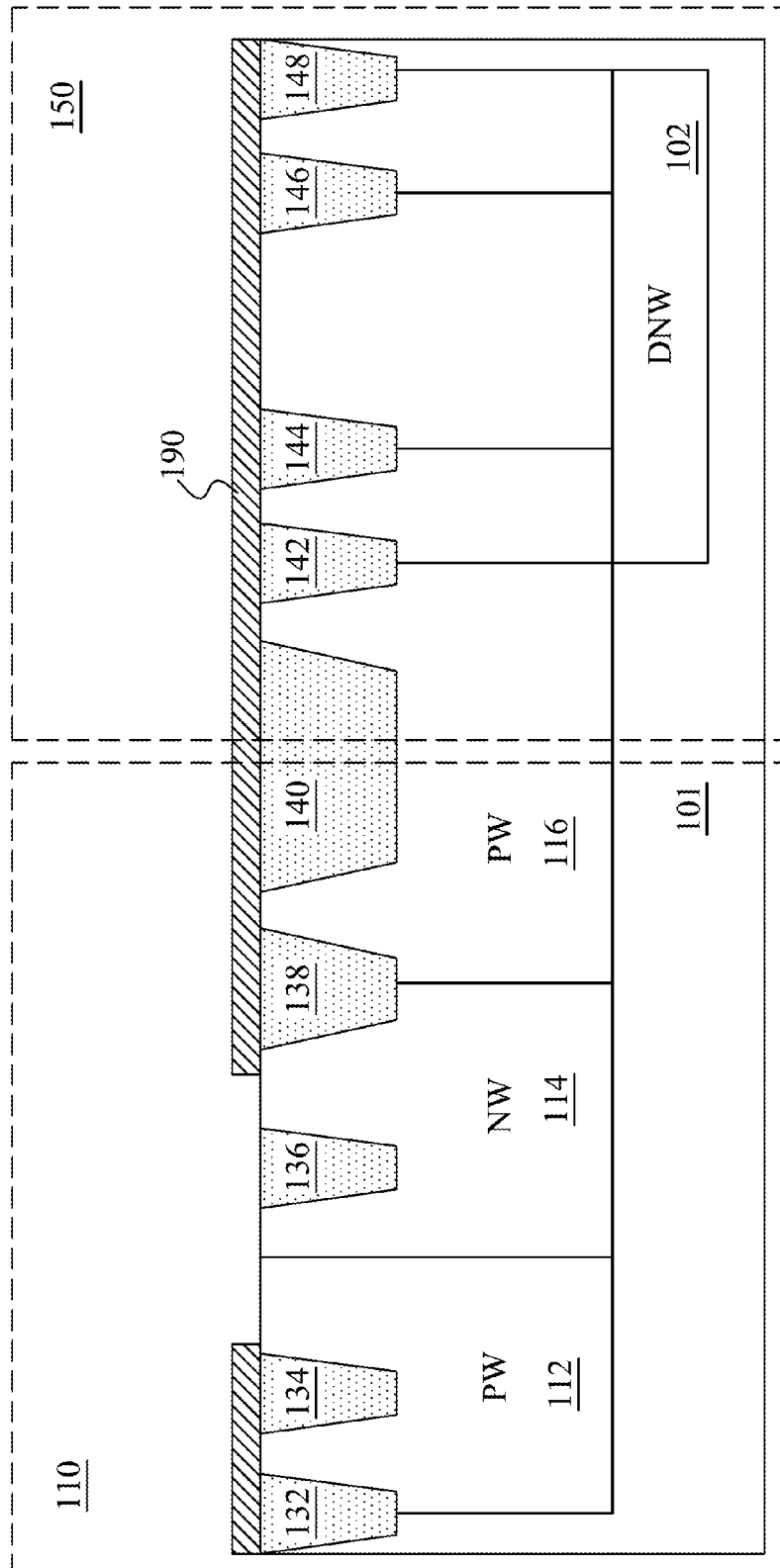


Fig. 4

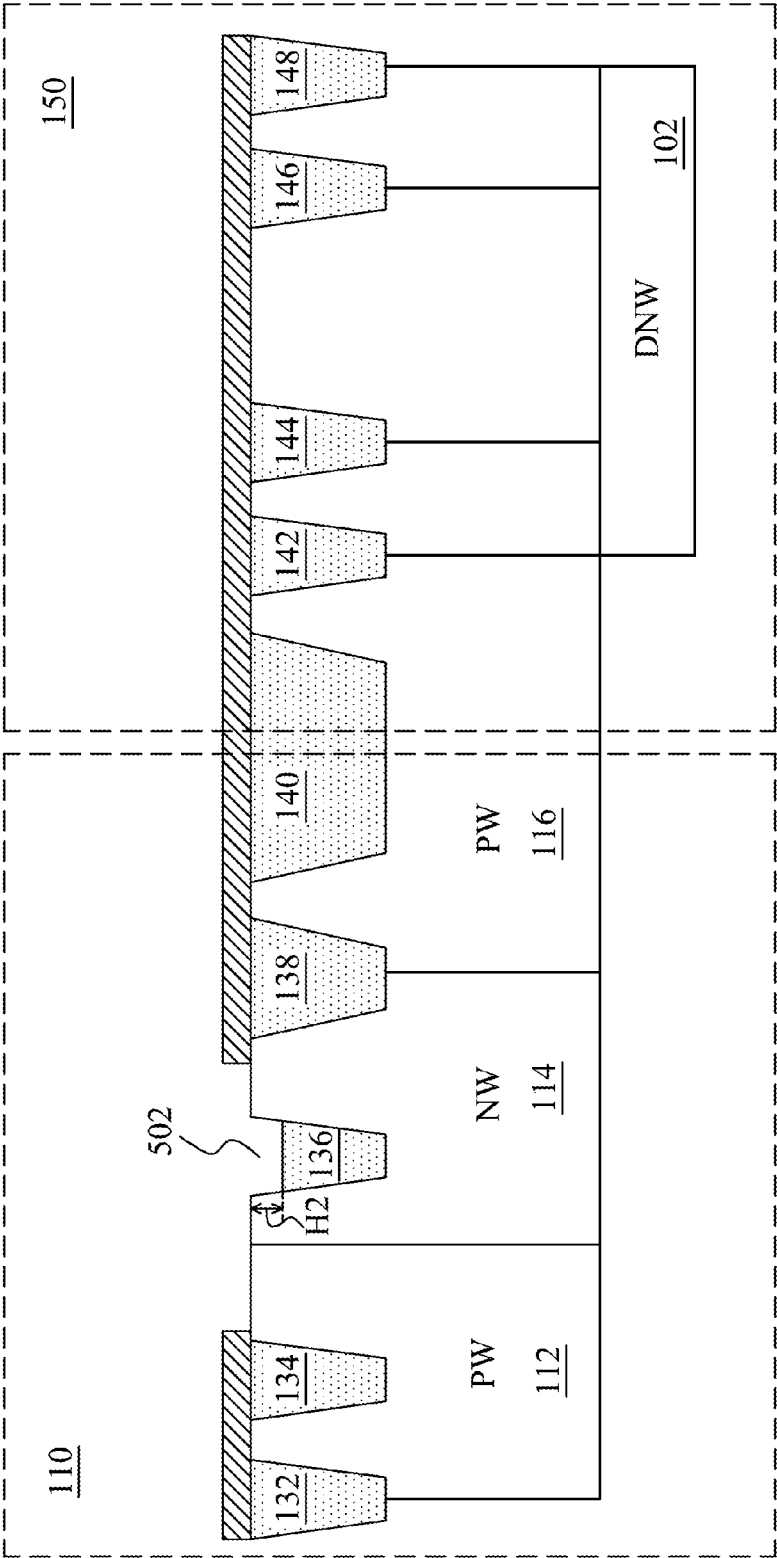


Fig. 5

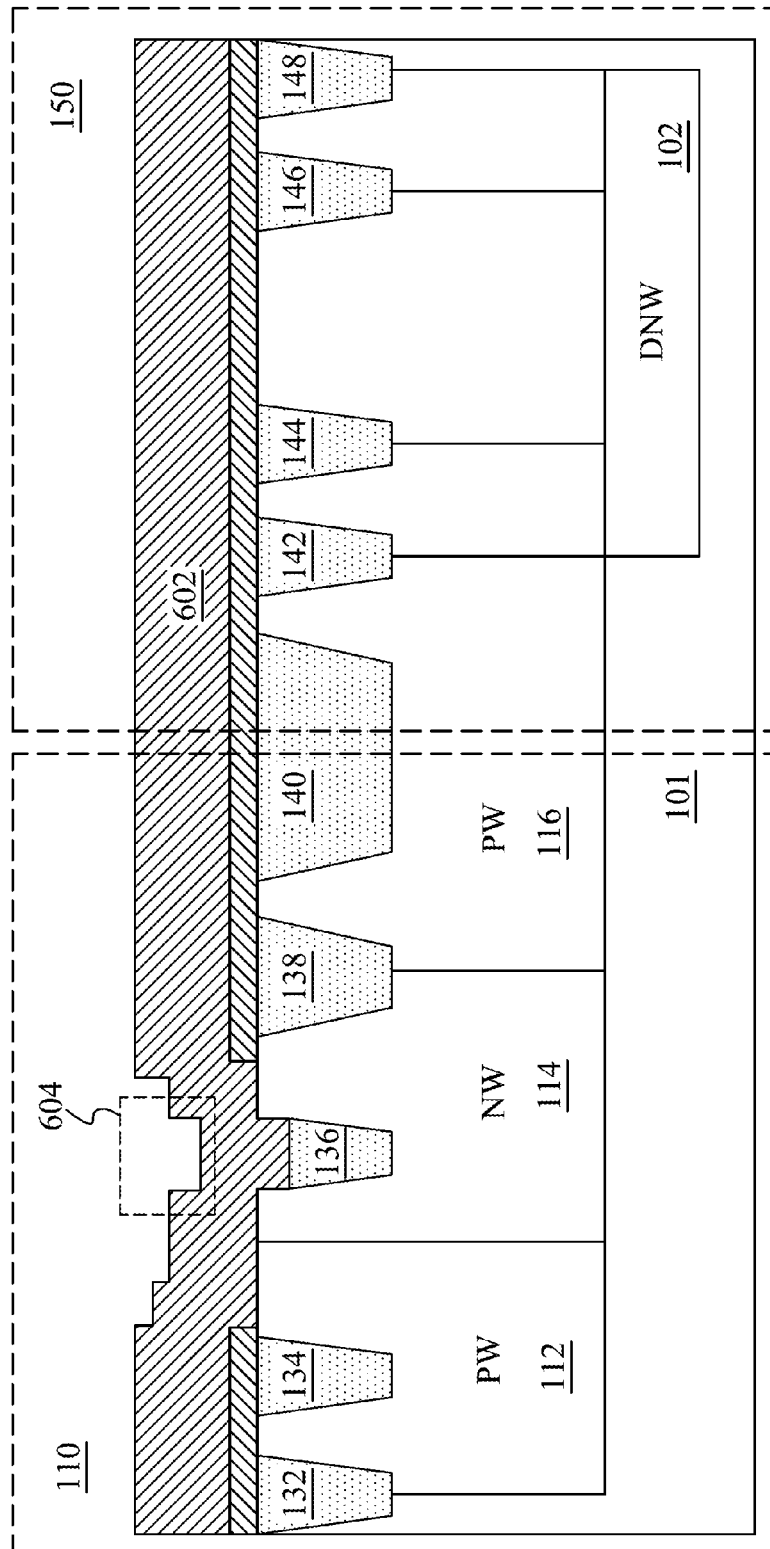


Fig. 6

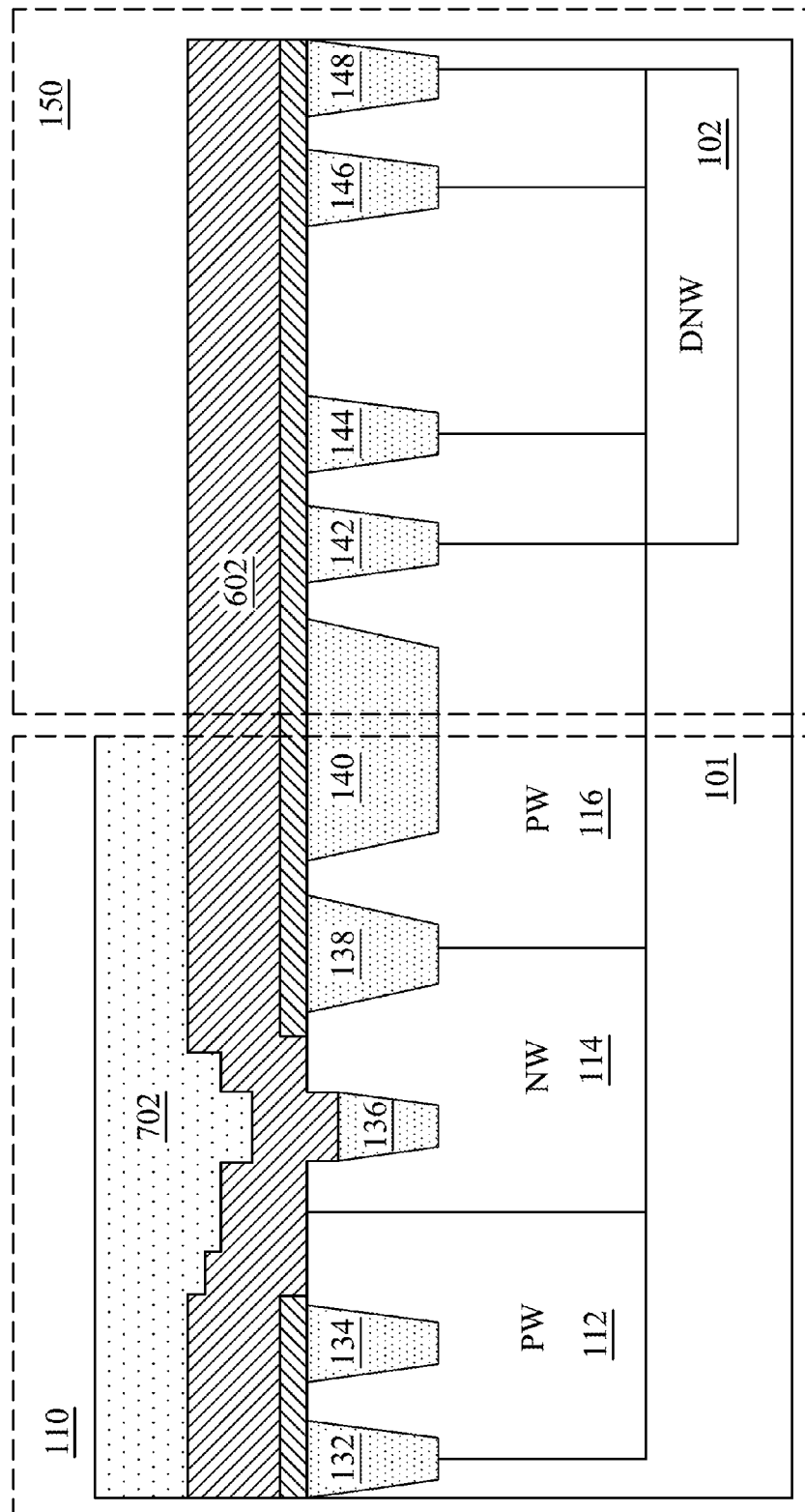


Fig. 7

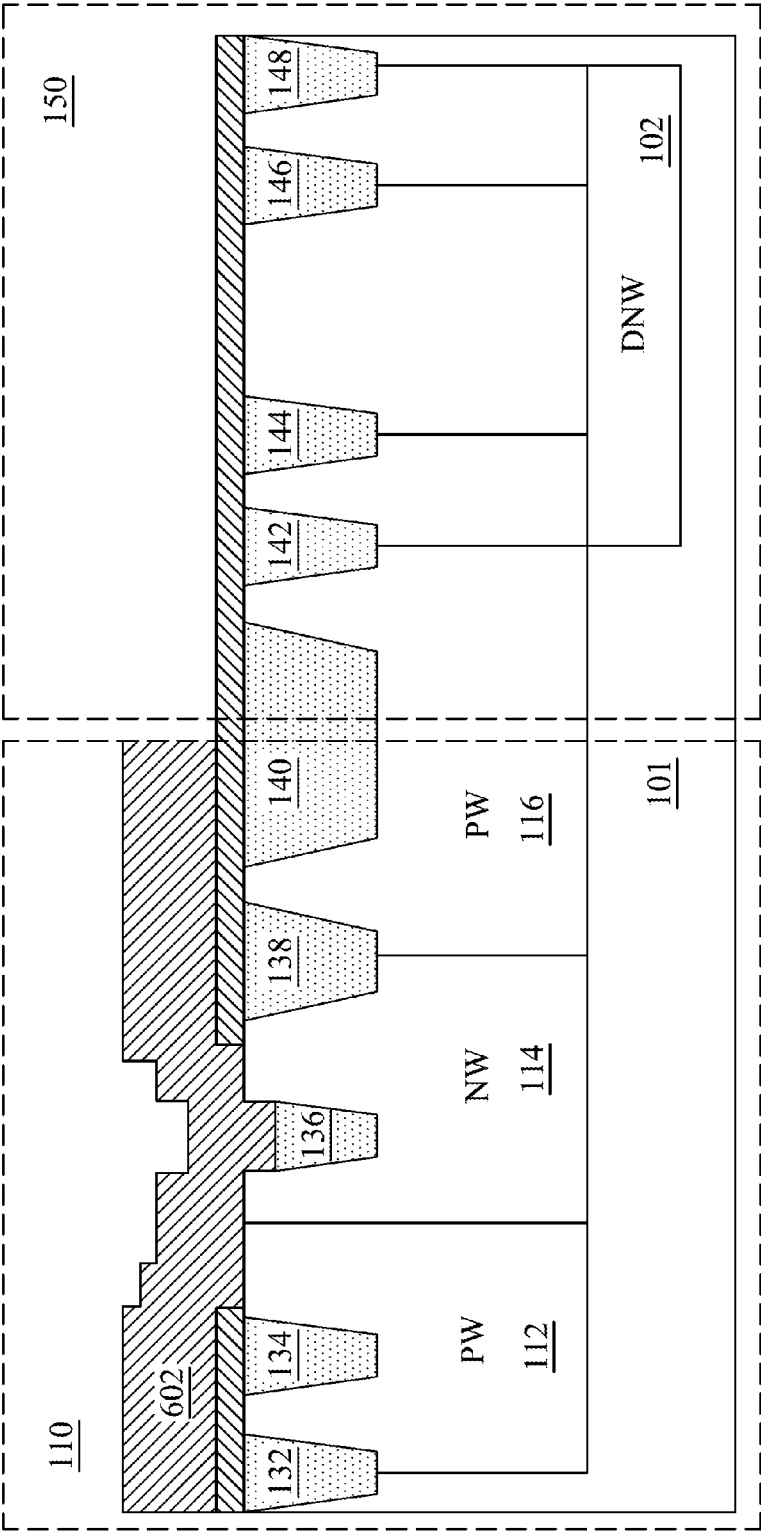


Fig. 8

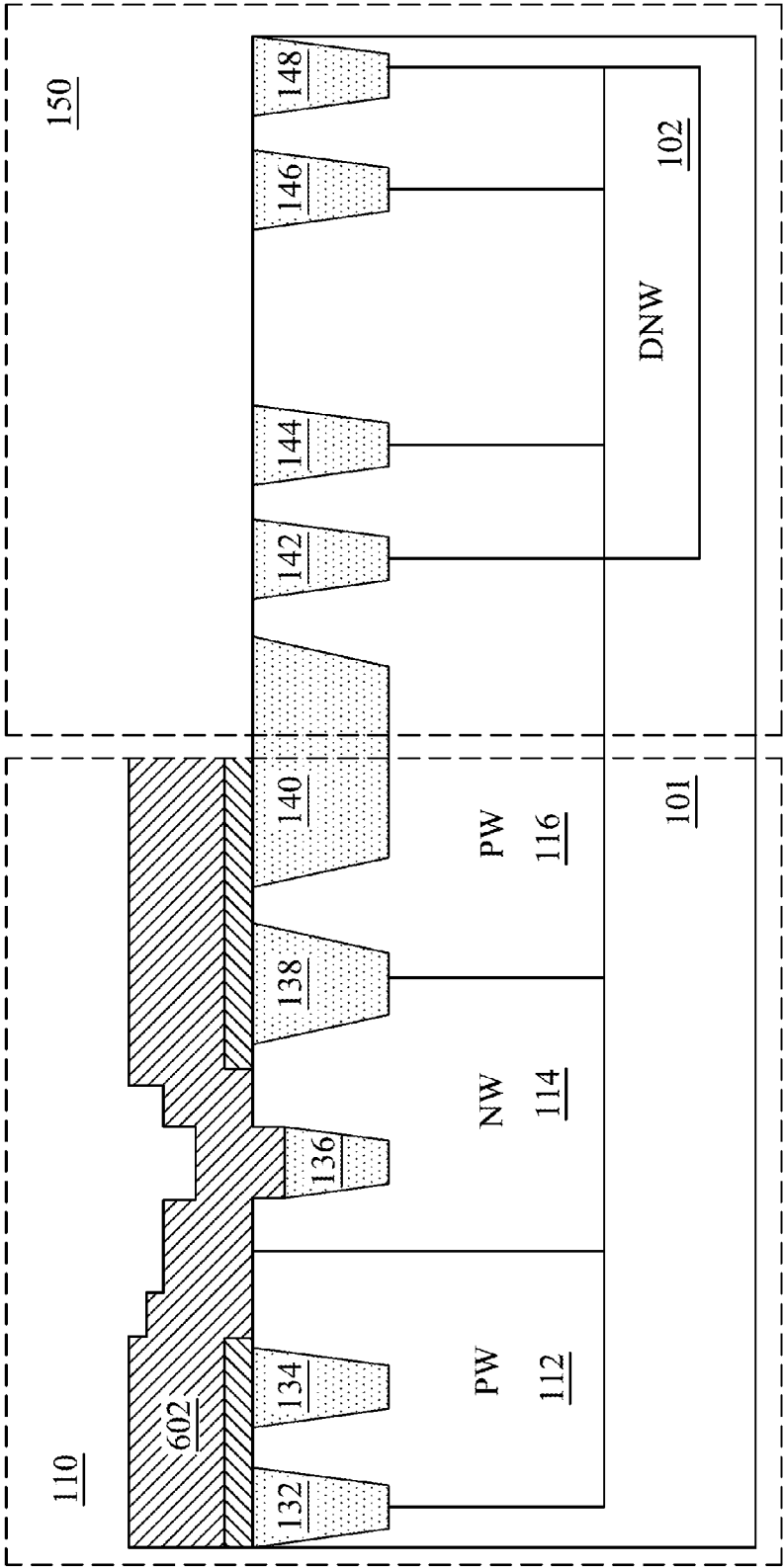


Fig. 9

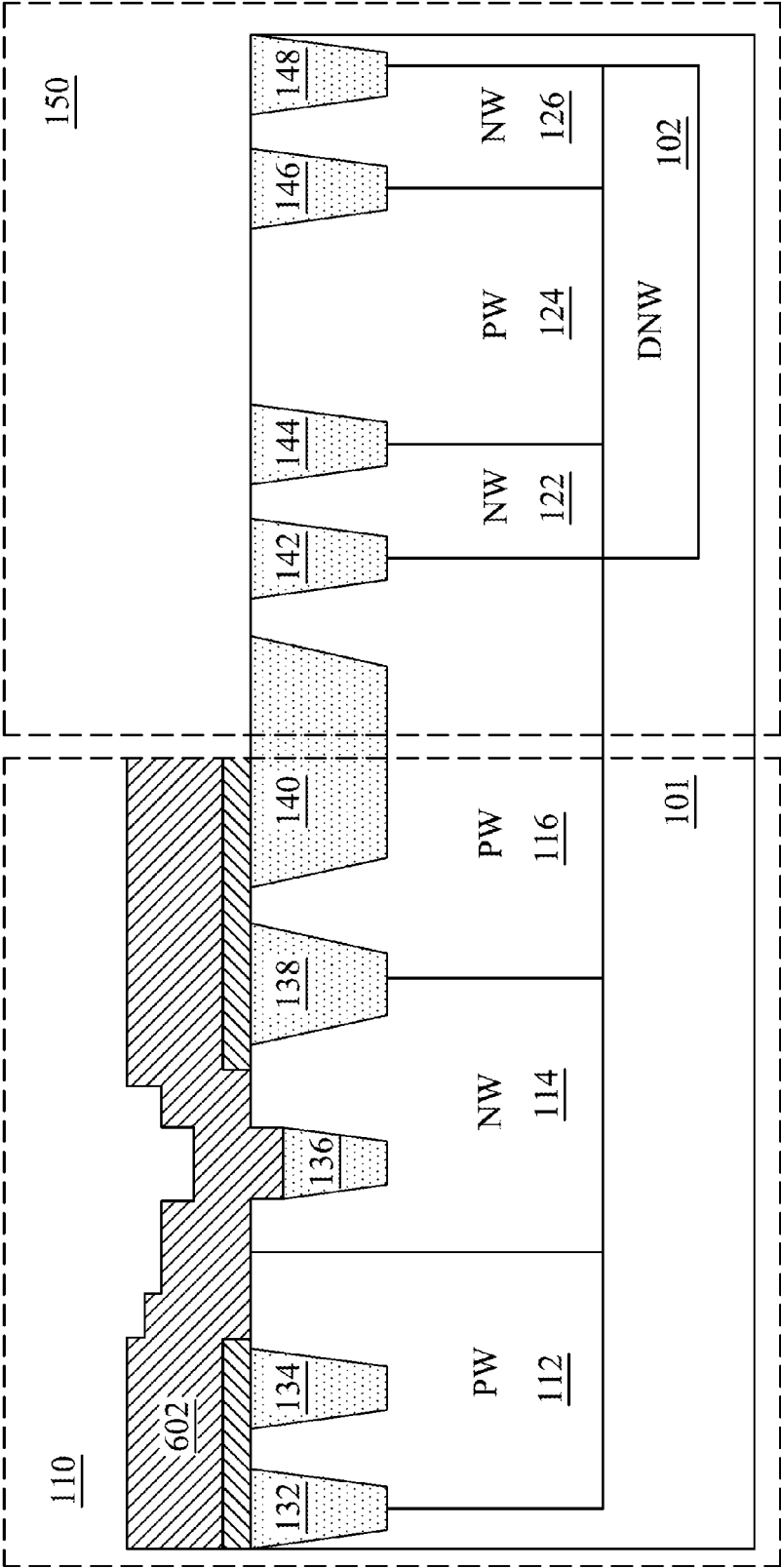


Fig. 10

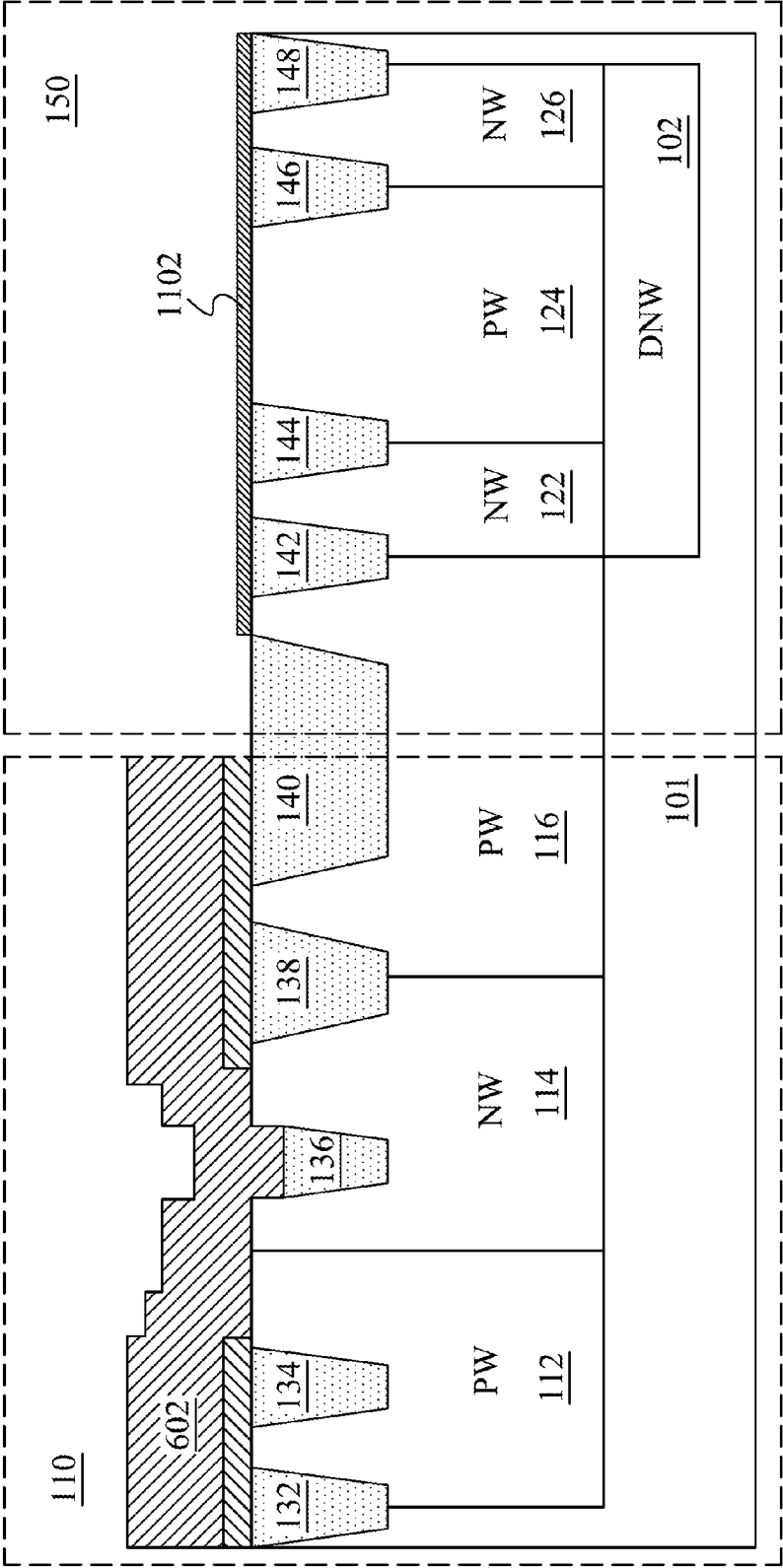


Fig. 11

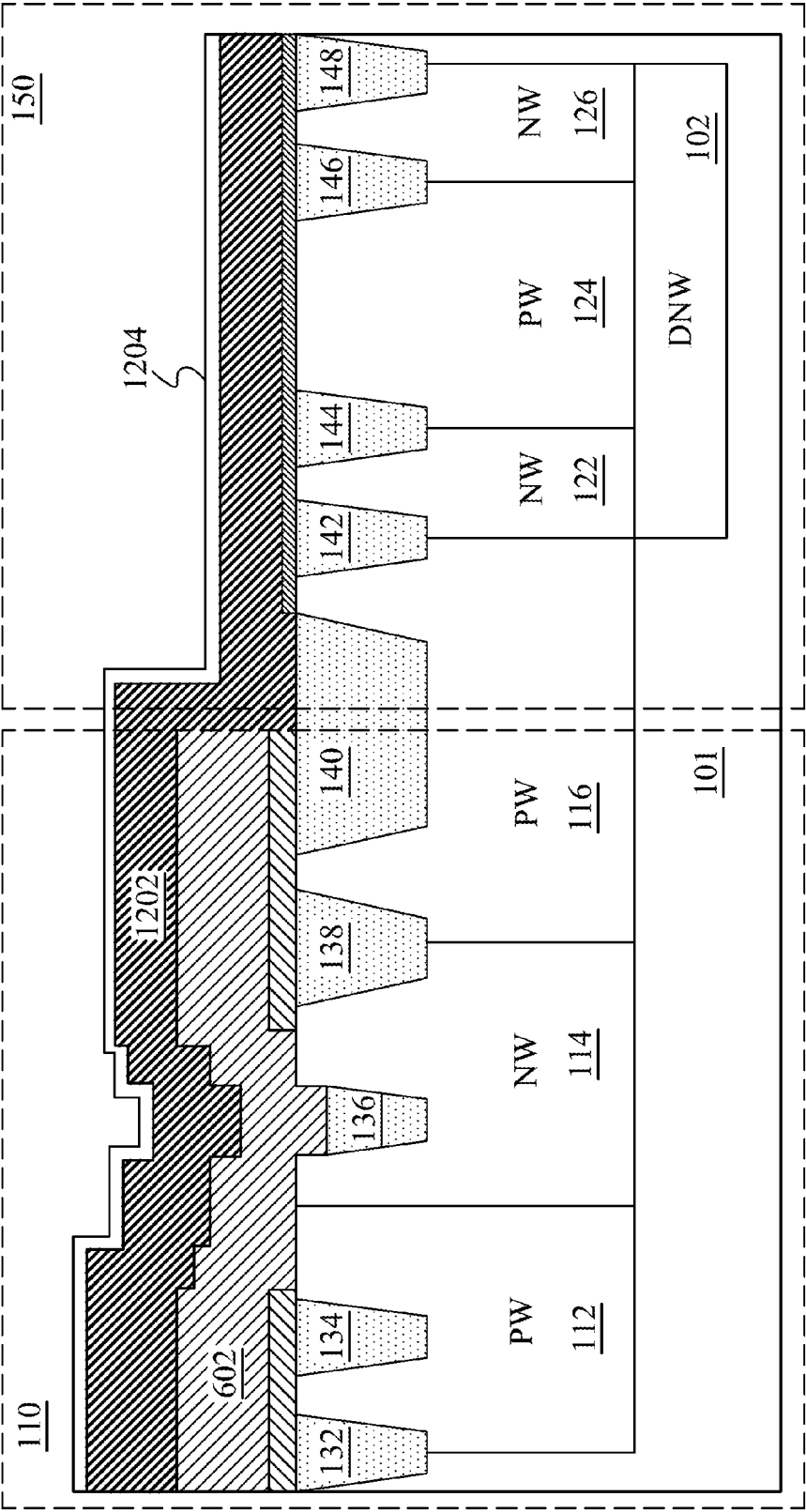


Fig. 12

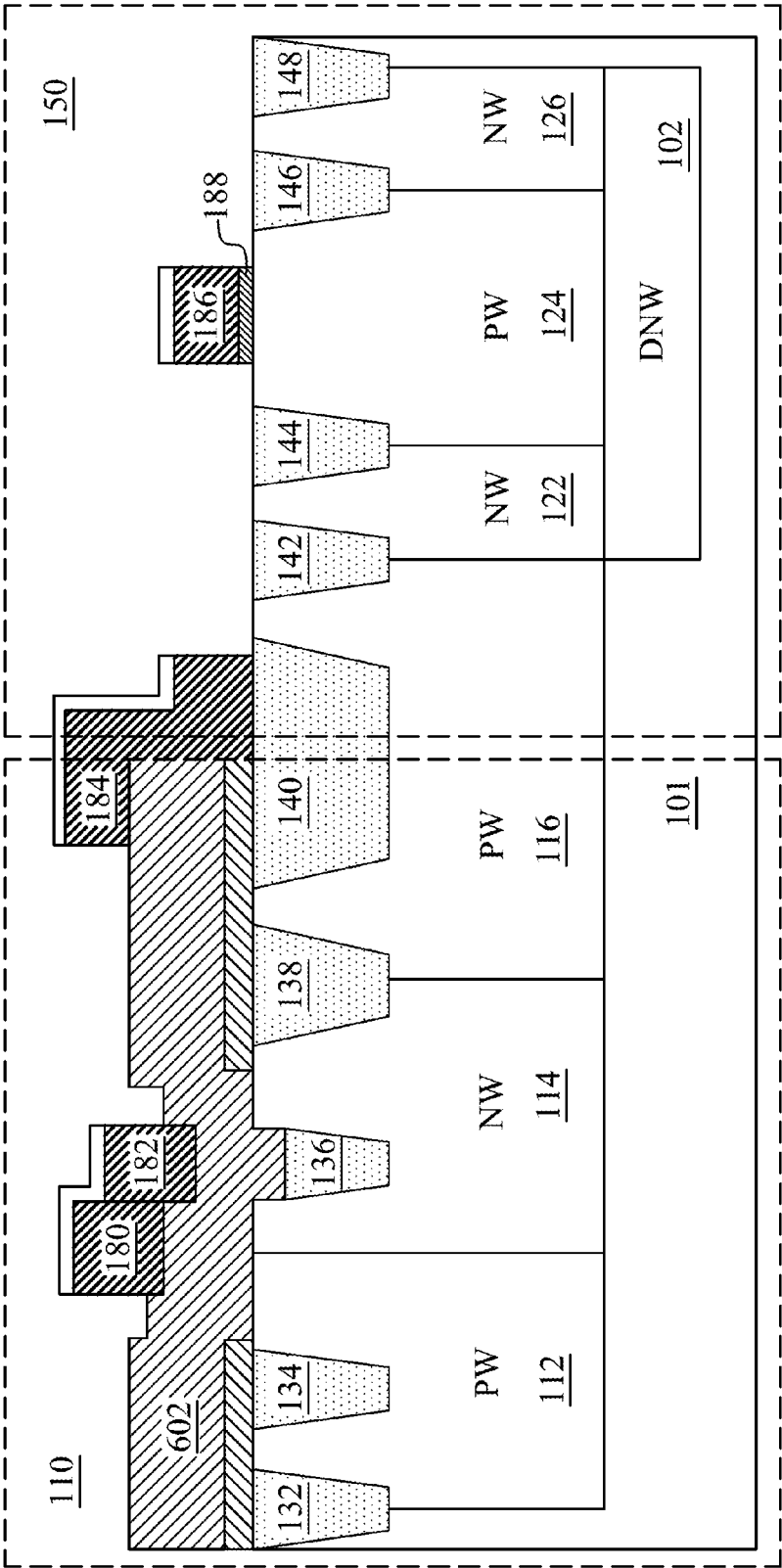


Fig. 13

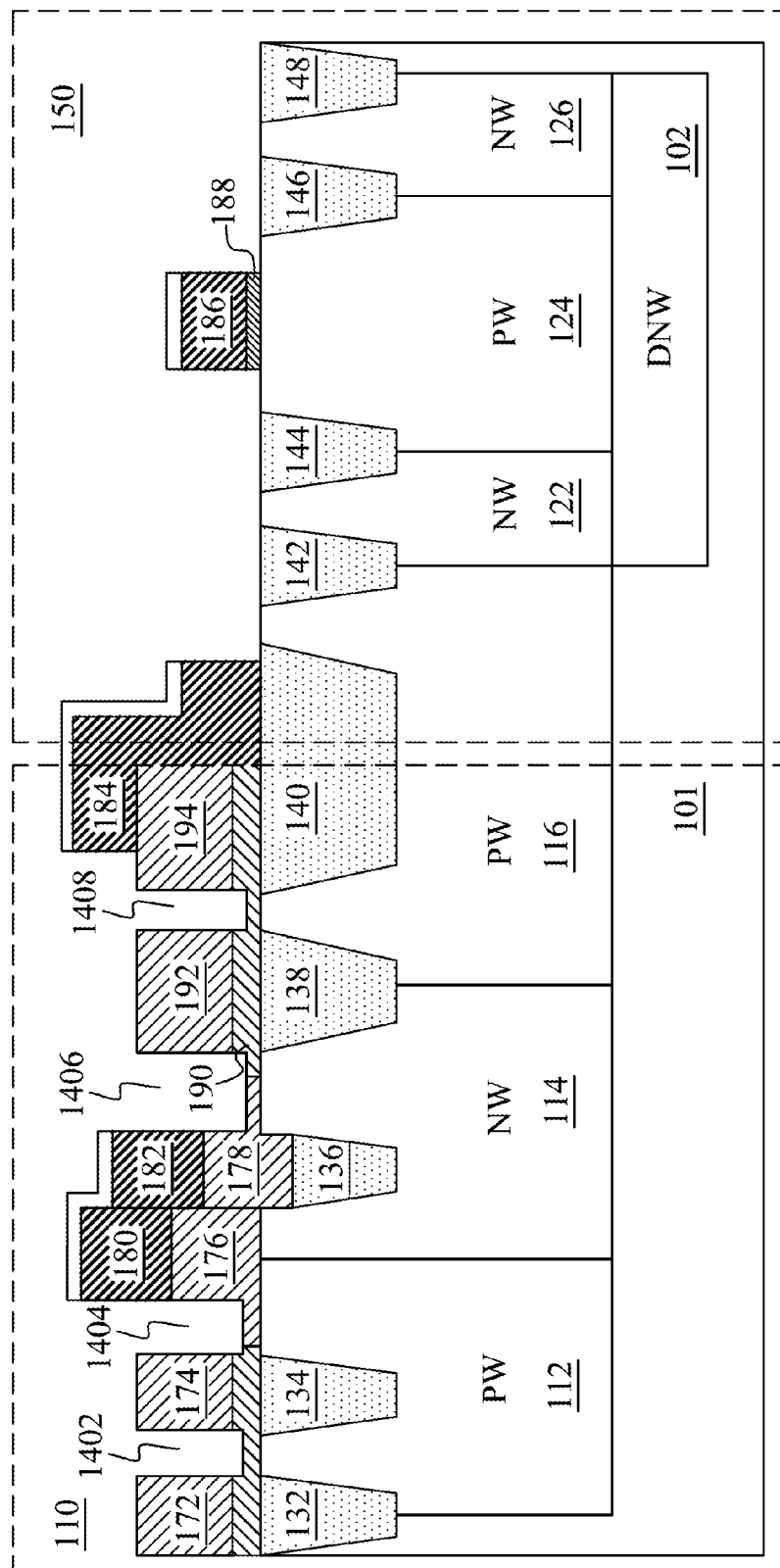


Fig. 14

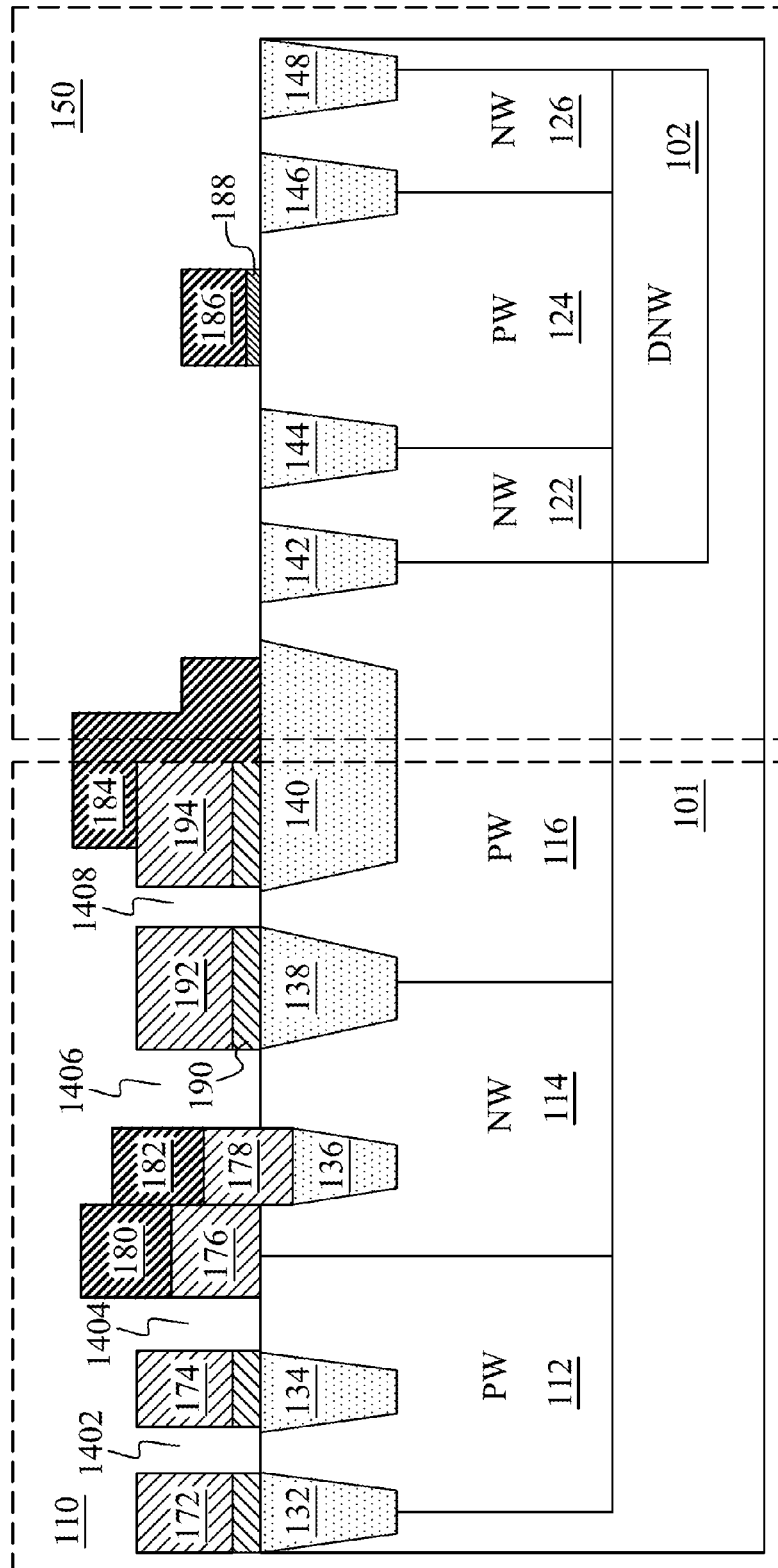


Fig. 15

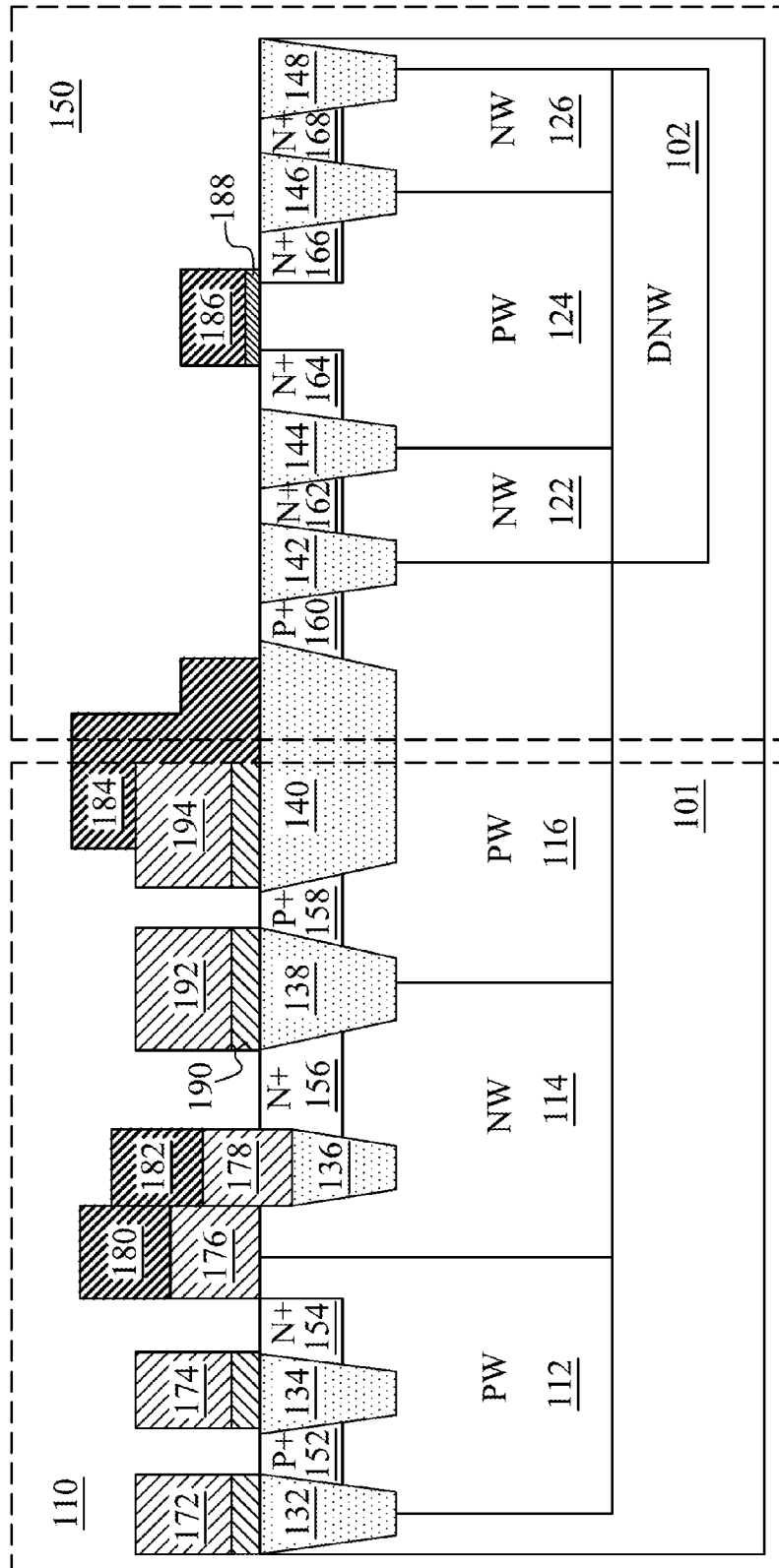


Fig. 16

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LATERAL MOSFET

BACKGROUND

The semiconductor industry has experienced rapid growth due to improvements in the integration density of a variety of electronic components (e.g., transistors, diodes, resistors, capacitors, etc.). For the most part, this improvement in integration density has come from shrinking the semiconductor process node (e.g., shrink the process node towards the sub-20 nm node). As semiconductor devices are scaled down, new techniques are needed to maintain the electronic components' performance from one generation to the next. For example, low on-resistance and high breakdown voltage of transistors are desirable for various high power applications.

As semiconductor technologies evolve, metal oxide semiconductor field effect transistors (MOSFET) have been widely used in today's integrated circuits. MOSFETs are voltage controlled devices. When a control voltage is applied to the gate of a MOSFET and the control voltage is greater than the threshold of the MOSFET, a conductive channel is established between the drain and the source of the MOSFET. As a result, a current flows between the drain and the source of the MOSFET. On the other hand, when the control voltage is less than the threshold of the MOSFET, the MOSFET is turned off accordingly.

According to the polarity difference, MOSFETs may include two major categories. One is n-channel MOSFETs; the other is p-channel MOSFETs. On the other hand, according to the structure difference, MOSFETs can be further divided into three sub-categories, planar MOSFETs, lateral diffused MOS (LDMOS) FETs and vertical diffused MOSFETs.

In comparison with other MOSFETs, the LDMOS transistor has more advantages. For example, the LDMOS transistor is capable of delivering more current per unit area because its asymmetric structure provides a short channel between the drain and the source of the LDMOS transistor.

BRIEF DESCRIPTION OF THE DRAWINGS

For a more complete understanding of the present disclosure, and the advantages thereof, reference is now made to the following descriptions taken in conjunction with the accompanying drawings, in which:

FIG. 1 illustrates a cross sectional view of a semiconductor device including a lateral diffusion metal oxide semiconductor (LDMOS) transistor in accordance with an embodiment;

FIG. 2 illustrates a cross sectional view of a semiconductor device after a dielectric layer is deposited over the substrate in accordance with an embodiment;

FIG. 3 illustrates a cross sectional view of the semiconductor device shown in FIG. 2 after a patterning process is applied to the semiconductor device in accordance with an embodiment;

FIG. 4 illustrates a cross sectional view of the semiconductor device shown in FIG. 3 after an etching process is applied to the semiconductor device in accordance with an embodiment;

FIG. 5 illustrates a cross sectional view of the semiconductor device shown in FIG. 4 after an etching process is applied to an isolation region of the semiconductor device in accordance with an embodiment;

FIG. 6 illustrates a cross sectional view of the semiconductor device shown in FIG. 5 after a high voltage gate dielectric layer is deposited over the substrate in accordance with an embodiment;

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FIG. 7 illustrates a cross sectional view of the semiconductor device shown in FIG. 6 after a photoresist layer is deposited over the high voltage gate dielectric layer in accordance with an embodiment;

FIG. 8 illustrates a cross sectional view of the semiconductor device shown in FIG. 7 after an etching process is applied to the high voltage gate dielectric layer in accordance with an embodiment;

FIG. 9 illustrates a cross sectional view of the semiconductor device shown in FIG. 8 after an etching process is applied to the dielectric layer in accordance with an embodiment;

FIG. 10 illustrates a cross sectional view of the semiconductor device shown in FIG. 9 after low voltage wells are formed in the low voltage region over the substrate in accordance with an embodiment;

FIG. 11 illustrates a cross sectional view of the semiconductor device shown in FIG. 10 after a thin dielectric layer is formed over the low voltage region in accordance with an embodiment;

FIG. 12 illustrates a cross sectional view of the semiconductor device shown in FIG. 11 after a gate electrode layer is deposited over the substrate in accordance with an embodiment;

FIG. 13 illustrates a cross sectional view of the semiconductor device shown in FIG. 12 after an etching process is applied to the top surface of the semiconductor device in accordance with an embodiment;

FIG. 14 illustrates a cross sectional view of the semiconductor device shown in FIG. 13 after an etching process is applied to the top surface of the semiconductor device in accordance with an embodiment;

FIG. 15 illustrates a cross sectional view of the semiconductor device shown in FIG. 14 after an etching process is applied to the top surface of the semiconductor device in accordance with an embodiment; and

FIG. 16 illustrates a cross sectional view of the semiconductor device shown in FIG. 15 after high voltage drain/source regions and low voltage drain/source regions are formed in accordance with an embodiment.

Corresponding numerals and symbols in the different figures generally refer to corresponding parts unless otherwise indicated. The figures are drawn to clearly illustrate the relevant aspects of the various embodiments and are not necessarily drawn to scale.

DETAILED DESCRIPTION OF ILLUSTRATIVE EMBODIMENTS

The making and using of the present embodiments are discussed in detail below. It should be appreciated, however, that the present disclosure provides many applicable inventive concepts that can be embodied in a wide variety of specific contexts. The specific embodiments discussed are merely illustrative of specific ways to make and use the embodiments of the disclosure, and do not limit the scope of the disclosure.

The present disclosure will be described with respect to embodiments in a specific context, a lateral metal oxide semiconductor field effect transistor (MOSFET). The embodiments of the disclosure may also be applied, however, to a variety of metal oxide semiconductor transistors. Hereinafter, various embodiments will be explained in detail with reference to the accompanying drawings.

FIG. 1 illustrates a cross sectional view of a semiconductor device including a lateral diffused metal oxide semiconductor (LDMOS) transistor in accordance with an embodiment. The LDMOS transistor **100** is formed in a substrate **101**. In accor-

dance with an embodiment, the substrate **101** may be formed of silicon, silicon germanium, silicon carbide or the like.

As shown in FIG. 1, there may be three wells formed in the substrate **101**. The wells are a first p-type well **112**, a first n-type well **114** and a second p-type well **116**. In particular, the first n-type well **114** is disposed between the first p-type well **112** and the second p-type well **116**.

The first p-type well **112** and the second p-type well **116** are formed by implanting p-type doping materials such as boron, gallium, aluminum, indium, combinations thereof, or the like. In accordance with an embodiment, a p-type material such as boron may be implanted to a doping density of about $10^{15}/\text{cm}^3$ to $10^{18}/\text{cm}^3$. Alternatively, the first p-type well **112** and the second p-type well **116** can be formed by a diffusion process.

Likewise, the first n-type well **114** are formed by implanting n-type doping materials such as phosphorous, arsenic, or the like. In accordance with an embodiment, an n-type material such as phosphorous may be implanted to a doping density of about $10^{15}/\text{cm}^3$ to $10^{18}/\text{cm}^3$. Alternatively, the first n-type well **114** can be formed by a diffusion process.

As shown in FIG. 1, there may be a plurality of isolation regions and active regions formed in the substrate **101**. The active regions include a first P+ region **152**, a first drain/source region **154**, a second drain/source region **156** and a second P+ region **158**. The drain/source regions as well as the P+ regions may form a LDMOS transistor.

In accordance with an embodiment, the wells (e.g., p-type wells **112**, **116** and n-type well **116**) shown in FIG. 1 are high voltage wells. As a result, the LDMOS transistor **100** is a high voltage transistor. Such a high voltage transistor can be used in medium voltage applications having a voltage rating range from about 2V to about 8V. Alternatively, such a high voltage transistor can be used in high voltage applications in a range from about 8V to about 400V. Furthermore, such a high voltage transistor may be used in ultra-high voltage applications having a voltage rating greater than 400V.

The isolation regions shown in FIG. 1 provide isolation between active regions. For example, the isolation region **132** is formed at an interface in the substrate **101** between the first n-type well **112** and an exterior well or component. The isolation region **134** is employed to isolate active regions (e.g., the first P+ region **152** and the first drain/source region **154**) so as to prevent leakage current from flowing between adjacent active regions.

The isolation region **136** functions as a reduced surface field (RESURF) structure. More particularly, the isolation region **136** is an extension of the second drain/source region **156**. Such a dielectric extension of the second drain/source region **156** helps to achieve a uniform electric field distribution. As a result, the LDMOS transistor **100** may achieve both higher breakdown voltage and lower on resistance.

It should be noted that a top surface of the isolation region **138** is lower than the top surfaces of other isolation regions (e.g., isolation regions **132** and **134**). The gap between the top surface of the isolation region **136** and the top surface of the substrate **101** is filled with a gate dielectric material. The height of the gap is defined as H2 as shown in FIG. 1. The detailed formation process of the gap between the top surface of the isolation region **136** and the top surface of the substrate **101** will be described below with respect to FIG. 5.

The isolation region **138** is formed between the second drain/source region **156** and the second P+ region **158**. The isolation region **140** is formed adjacent to the second P+ region **158**. The function and structure of the isolation regions **138** and **140** are similar to the function and structure of

isolation regions **134** and **132** respectively, and hence are not discussed in detail herein to avoid unnecessary repetition.

The isolation regions (e.g., isolation regions **132**, **134**, **136**, **138** and **140**) can be formed by various suitable fabrication techniques (e.g., thermally grown, deposited) and a variety of materials (e.g., silicon oxide, silicon nitride, any combinations thereof and/or the like). In this embodiment, the isolation region **104** may be fabricated by using a shallow trench isolation (STI) technique.

A gate dielectric layer is deposited over the substrate **101**. In order to form active regions through ion implantation techniques, there may be a plurality of openings formed between two adjacent gate dielectric blocks. For example, in order to form the first P+ region **152**, there is an opening between a first gate dielectric block **172** and a second gate dielectric block **174**. Likewise, a third gate dielectric block **192** and a fourth gate dielectric block **194** are formed. The detailed process of forming openings in the gate dielectric layer will be described below with respect to FIGS. 14-16.

A gate electrode layer is formed over the substrate **101**. As shown in FIG. 1, the gate electrode layer may be divided into two portions, namely a first gate electrode layer **180** and a second gate electrode layer **182**. As shown in FIG. 1, the first gate electrode layer **180** is formed over a first gate dielectric region **176**, which is formed on the top surface of the substrate **101**. The second gate electrode layer **182** is formed over a second gate dielectric region **178**. The second gate electrode layer **182** is vertically aligned with the isolation region **136**. More particularly, due to the gap between the isolation region **136** and the top surface of the substrate **101**, there is a height difference between the top surface of the first gate electrode layer **180** and the top surface of the second gate electrode layer **182**. The height difference shown in FIG. 1 is defined as H1. In accordance with an embodiment, H1 is in a range from about 300 Angstroms to about 500 Angstroms.

One skilled in the art will recognize that FIG. 1 illustrates an ideal profile. H1 and H2 may vary after subsequent fabrication processes. The height difference (e.g., H1 and H2) shown in FIG. 1 is used to illustrate the inventive aspects of the various embodiments. The disclosure is not limited to any particular height difference.

It should be noted that the height of the first gate electrode layer **180** is similar to the height of conventional LDMOS transistors' gate electrode layer. Without having a recess at the isolation region **136**, the top surface of the second gate electrode layer **182** may be higher than the top surface of conventional LDMOS transistors' gate electrode layer. The protruded second electrode layer **182** may lead to a short between the second electrode layer **182** and subsequently formed metal layers (e.g., a first metal layer M1).

One advantageous feature of having the second gate electrode layer **182** with a lower top surface is that the lower top surface of the second gate electrode **182** helps to prevent the second gate electrode layer **182** from shorting with subsequently formed metal layers (e.g., a first metal layer M1). As a result, the process margin of the LDMOS transistor **100** can be improved. The improved process margin may further simplify the fabrication process and reduce the manufacturing cost of the LDMOS transistor **100**.

FIGS. 2-16 illustrates cross sectional views of intermediate steps of fabricating a semiconductor device including the LDMOS transistor shown in FIG. 1 in accordance with an embodiment. FIG. 2 illustrates a cross sectional view of a semiconductor device after a dielectric layer is deposited over the substrate **101** in accordance with an embodiment. The

substrate **101** can be a semiconductor substrate, such as a bulk silicon substrate, a semiconductor on insulator (SOI), or the like.

The substrate **101** may include two regions, namely a high voltage region **110** and a low voltage region **150**. The high voltage region **110** and the low voltage region **150** are demarcated in this example by two dashed rectangles. The low voltage region **150** comprises isolation regions **142**, **144**, **146** and **148** as shown in FIG. 2. The substrate **101** can be doped with various wells, such as according to appropriate high voltage and low voltage applications. In the high voltage region **110**, a first p-type well **112**, a first n-type well **114** and a second p-type well **116** are formed in the substrate **101**.

The high voltage region **110** is used to form a high voltage LDMOS transistor. Likewise, the low voltage region **150** is used to form a low voltage planar transistor. The detailed formation process of the high voltage LDMOS transistor and low voltage planar transistor will be described below with respect to FIGS. 3-16.

As shown in FIG. 2, a dielectric layer **190** is formed over the substrate **101**. The dielectric layer **190** may be formed of various dielectric materials commonly used in integrated circuit fabrication. For example, the dielectric layer **190** may be formed of silicon dioxide, silicon nitride or a doped glass layer such as boron silicate glass and the like. Alternatively, dielectric layer may be a silicon oxynitride layer, a polyamide layer, a low dielectric constant insulator and/or the like. In addition, a combination of the foregoing dielectric materials may also be used to form the dielectric layer **190**.

In accordance with an embodiment, the dielectric layer **190** may be formed of silicon nitride. The silicon nitride layer **190** may be formed using suitable deposition techniques such as chemical vapor deposition (CVD) and/or the like.

FIG. 3 illustrates a cross sectional view of the semiconductor device shown in FIG. 2 after a patterning process is applied to the semiconductor device in accordance with an embodiment. In accordance with an embodiment, a photoresist mask layer **302** is deposited over the dielectric layer **190** through suitable deposition techniques. Furthermore, in consideration with the location of the opening in the dielectric layer **190**, suitable photolithography techniques are employed to form an opening **304** in the photoresist layer **302**.

FIG. 4 and FIG. 5 illustrate a high voltage gate oxide pre-clean process in accordance with an embodiment. FIG. 4 illustrates a cross sectional view of the semiconductor device shown in FIG. 3 after an etching process is applied to the semiconductor device in accordance with an embodiment. An etching process, such as a reactive ion etch (RIE) or other dry etch, an anisotropic wet etch, or any other suitable anisotropic etch or patterning process, is performed to remove a portion of the dielectric layer **190**. The remaining photo resist layer (not shown) may be removed by using a suitable ashing process.

FIG. 5 illustrates a cross sectional view of the semiconductor device shown in FIG. 4 after an etching process is applied to an isolation region of the semiconductor device in accordance with an embodiment. A suitable etching technique such as a wet etching technique is applied to the upper portion of the isolation region **136**. As a result, the dielectric material filled in the upper portion of the isolation region **136** has been removed. By controlling the strength and direction of the etching process, a recess **502** is formed in the isolation region **136**. In accordance with an embodiment, the recess **502** is of a height H2. H2 is in a range from about 300 Angstroms to about 500 Angstroms.

FIG. 6 illustrates a cross sectional view of the semiconductor device shown in FIG. 5 after a high voltage gate dielectric

layer is deposited over the substrate in accordance with an embodiment. The high voltage gate dielectric layer **602** is conformally deposited over the substrate **101**. The high voltage gate dielectric layer **602** may be formed by using suitable deposition techniques such as CVD and/or the like.

In accordance with various embodiments, the high voltage gate dielectric layer **602** may be formed of an oxide, such as silicon oxide, silicon nitride, composite oxide/nitride/oxide, the like, or a combination thereof. Other acceptable materials can be used for the high voltage gate dielectric layer **602**. The thickness of the high voltage gate dielectric layer **602** is in a range from about 250 Å to about 4,000 Å.

It should be noted that the high voltage gate dielectric layer **602** is of an uneven surface (e.g., the region highlighted by a dashed rectangle **604**) due to the recess **502** (shown in FIG. 5) in the isolation region **136**. It should further be noted that the high voltage dielectric layer **602** may be of a multiple layer structure. Alternatively, the high voltage dielectric layer **602** may comprise different dielectric materials.

FIG. 7 illustrates a cross sectional view of the semiconductor device shown in FIG. 6 after a photoresist layer is deposited over the high voltage dielectric layer in accordance with an embodiment. A photoresist layer **702** is deposited over the high voltage gate dielectric layer **602** using a spin on deposition and/or the like. The photoresist layer **702** is exposed and developed such that only the portion over the high voltage region **110** remains. The remaining photoresist layer **702** laterally extends from the isolation region **132** to the isolation region **140**. The portion of the high voltage gate dielectric layer **602** over the low voltage region **150** is exposed by the photoresist layer **702**.

FIG. 8 illustrates a cross sectional view of the semiconductor device shown in FIG. 7 after an etching process is applied to the high voltage gate dielectric layer in accordance with an embodiment. An etching process is applied to the semiconductor device. As shown in FIG. 8, the portion of the high voltage gate dielectric layer **602** over the low voltage region **150** has been removed as a result.

FIG. 9 illustrates a cross sectional view of the semiconductor device shown in FIG. 8 after an etching process is applied to the dielectric layer in accordance with an embodiment. An etching process is applied to the semiconductor device. As shown in FIG. 9, the portion of the dielectric layer **190** over the low voltage region **150** has been removed as a result.

FIG. 10 illustrates a cross sectional view of the semiconductor device shown in FIG. 9 after low voltage wells are formed in the low voltage region over the substrate in accordance with an embodiment. Similar to the doping process shown in FIG. 2, the low voltage region **150** may be doped with various wells. As shown in FIG. 10, in the low voltage region **150**, n-type wells **122**, **126** and p-type well **124** are formed in a deep n-type well (DNW) **102**, which is formed in the substrate **101**.

FIG. 11 illustrates a cross sectional view of the semiconductor device shown in FIG. 10 after a thin dielectric layer is formed over the low voltage region in accordance with an embodiment. The thin dielectric layer **1102** is a low voltage gate dielectric layer. The low voltage gate dielectric layer **1102** is formed by using suitable fabrication techniques such as, thermal oxidation and/or the like.

In accordance with an embodiment, the low voltage gate dielectric layer **1102** comprises an oxide, such as silicon oxide. Alternatively, the low voltage gate dielectric layer **1102** can comprise hafnium oxide, tantalum oxide, aluminum oxide, the like, or a combination thereof. The low voltage gate dielectric layer **1102** has a thickness in a range from about 15 Å to about 150 Å.

It should be noted while FIG. 11 shows the low voltage gate dielectric layer 1102 is a single layer, the low voltage gate dielectric layer 1102 can be of a multiple layer structure. Alternatively, the low voltage gate dielectric layer 1102 may comprise multiple dielectric materials. It should further be noted that the thickness of the high voltage gate dielectric layer 602 is greater than the thickness of the low voltage gate dielectric layer 1102.

FIG. 12 illustrates a cross sectional view of the semiconductor device shown in FIG. 11 after a gate electrode layer is deposited over the substrate in accordance with an embodiment. The gate electrode layer 1202 may be formed of polysilicon. Alternatively, the gate electrode layer 1202 may be formed of other commonly used conductive materials such as a metal (e.g., tantalum, titanium, molybdenum, tungsten, platinum, aluminum, hafnium, ruthenium), a metal silicide (e.g., titanium silicide, cobalt silicide, nickel silicide, tantalum silicide), a metal nitride (e.g., titanium nitride, tantalum nitride), doped poly-crystalline silicon, other conductive materials, combinations thereof, or the like.

The gate electrode layer is deposited over the high voltage gate dielectric layer 602 and low voltage gate dielectric layer 1102 using suitable deposition techniques such as CVD and/or the like. The gate electrode layer 1202 can subsequently be used to form gate electrodes for transistor devices in the high voltage region 110 and transistor devices in the low voltage region 150.

A bottom anti-reflection coating (BARC) layer 1204 is formed over the gate electrode layer 1202. The BARC layer 1204 may be formed of a nitride material, an organic material, an oxide material and the like. The BARC layer 1204 may be formed using suitable techniques such as CVD and/or the like.

It should be noted that the gate electrode layer 1202 over the high voltage region 110 is of an uneven surface due to the uneven surface of the high voltage gate electric layer shown in FIG. 6.

FIG. 13 illustrates a cross sectional view of the semiconductor device shown in FIG. 12 after an etching process is applied to the top surface of the semiconductor device in accordance with an embodiment. The gate electrode layer 1202 is patterned to form a high voltage gate electrode layer including a first portion 180 and a second portion 182, a low voltage gate electrode 186 formed over a low voltage gate dielectric layer 188 and a dummy structure 184 at a boundary between the high voltage region 110 and the low voltage region 150. The high voltage gate electrode is of an even surface. In particular, the top surface of the second portion 182 is lower than the top surface of the first portion 180. Such a lower top surface helps to prevent a short between the high voltage gate electrode and subsequently formed metal layers (not shown).

FIG. 14 illustrates a cross sectional view of the semiconductor device shown in FIG. 13 after an etching process is applied to the top surface of the semiconductor device in accordance with an embodiment. The high voltage gate dielectric layer 602 may be patterned, such as by anisotropically etching to form the openings 1402, 1404, 1406 and 1408 as illustrated in FIG. 14.

FIG. 15 illustrates a cross sectional view of the semiconductor device shown in FIG. 14 after an etching process is applied to the top surface of the semiconductor device in accordance with an embodiment. In order to apply an ion implantation process to the high voltage region 110, an anisotropic etching process is applied to the openings 1402, 1404, 1406 and 1408 in accordance with an embodiment. As a

result, the dielectric materials at the bottoms of the openings 1402, 1404, 1406 and 1408 have been removed.

A BARC removal process may be applied to the semiconductor device when the etching process is applied to the top surface of the semiconductor device. The BARC layer may be removed by using suitable etching techniques including dry etching, wet etching, a combination thereof and/or the like.

FIG. 16 illustrates a cross sectional view of the semiconductor device shown in FIG. 15 after high voltage drain/source regions and low voltage drain/source regions are formed in accordance with an embodiment. In high voltage region 110, the drain/source regions 154 and 156 may be formed over the substrate 101 on opposing sides of the isolation region 136. The first P+ region 152 is formed between the isolation region 132 and isolation region 134. The second P+ region 158 is formed between the isolation region 138 and the isolation region 140.

In accordance with an embodiment, when the substrate 101 is an n-type substrate, the drain/source regions (e.g., drain/source region 154) may be formed by implanting appropriate p-type dopants such as boron, gallium, indium, or the like. Alternatively, in an embodiment in which the substrate 101 is a p-type substrate, the drain/source regions (e.g., drain/source region 154) may be formed by implanting appropriate n-type dopants such as phosphorous, arsenic, or the like. In accordance with an embodiment, the doping density of the drain/source regions (e.g., drain/source region 154) is in a range from about $10^{19}/\text{cm}^3$ to about $5 \times 10^{19}/\text{cm}^3$. It should be noted while FIG. 16 illustrates the drain/source regions are n-type, the drain/source regions may be p-type depending on different design needs.

In the low voltage region 150, the drain/source regions (e.g., N+ regions 164 and 166) may be formed over the substrate 101. N+ region 162 and 168, and P+ region 160 are formed over the substrate 101 as shown in FIG. 16. In accordance with an embodiment, when the substrate 101 is an n-type substrate, the drain/source regions (e.g., drain/source region 164) may be formed by implanting appropriate p-type dopants such as boron, gallium, indium, or the like. Alternatively, in an embodiment in which the substrate 101 is a p-type substrate, the drain/source regions (e.g., drain/source region 164) may be formed by implanting appropriate n-type dopants such as phosphorous, arsenic, or the like. In accordance with an embodiment, the doping density of the drain/source regions (e.g., drain/source region 164) is in a range from about $10^{19}/\text{cm}^3$ to about $5 \times 10^{19}/\text{cm}^3$. It should be noted while FIG. 16 illustrates the low voltage drain/source regions are n-type, the low voltage drain/source regions may be p-type depending on different design needs.

Although embodiments of the present disclosure and its advantages have been described in detail, it should be understood that various changes, substitutions and alterations can be made herein without departing from the spirit and scope of the disclosure as defined by the appended claims.

Moreover, the scope of the present application is not intended to be limited to the particular embodiments of the process, machine, manufacture, composition of matter, means, methods and steps described in the specification. As one of ordinary skill in the art will readily appreciate from the present disclosure, processes, machines, manufacture, compositions of matter, means, methods, or steps, presently existing or later to be developed, that perform substantially the same function or achieve substantially the same result as the corresponding embodiments described herein may be utilized according to the present disclosure. Accordingly, the appended claims are intended to include within their scope

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such processes, machines, manufacture, compositions of matter, means, methods, or steps.

What is claimed is:

1. A semiconductor device comprising:

a plurality of isolation regions formed in a substrate having
a top surface, wherein a first isolation region of the
plurality of isolation regions has a top surface lower than
the top surface of the substrate; and

a gate electrode layer comprising:

a first gate electrode layer formed over the first isolation
region; and

a second gate electrode layer formed over the top surface
of the substrate, wherein a bottom surface of the first
gate electrode layer is lower than a bottom surface of
the second gate electrode layer.

2. The semiconductor device of claim 1, wherein:

a high voltage gate dielectric layer comprising:

a first high voltage gate dielectric layer formed over the
first isolation region; and

a second high voltage gate dielectric layer formed over
the top surface of the substrate, wherein a top surface
of the first high voltage gate dielectric layer is lower
than a top surface of the second high voltage gate
dielectric layer.

3. The semiconductor device of claim 2, wherein:

the high voltage gate dielectric layer comprises two or
more different dielectric materials.

4. The semiconductor device of claim 1, wherein:

the isolation region is a shallow trench isolation (STI)
region.

5. The semiconductor device of claim 1, wherein:

the first gate electrode layer forms a gate structure of a high
voltage lateral diffused transistor.

6. The semiconductor device of claim 1, wherein:

the gate electrode layer comprises polysilicon.

7. The semiconductor device of claim 1, wherein:

the isolation region comprises two or more different dielec-
tric materials.

8. The semiconductor device of claim 1, wherein:

the first isolation region is a reduced surface field (RE-
SURF) STI.

9. A device comprising:

a first device formed in a substrate, wherein the first device
comprises:

a first gate dielectric layer formed over a first isolation
region, wherein the first gate dielectric layer has a
portion below a top surface of the substrate, and
wherein a top surface of the first isolation region is
lower than a top surface of the substrate; and

a first gate electrode layer formed over the first gate
dielectric layer, wherein the first gate electrode layer
comprises:

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a first portion vertically aligned with the first isolation
region; and

a second portion immediately contiguous to the first
portion, wherein a bottom surface of the first por-
tion is lower than a bottom surface of the second
portion.

10. The device of claim 9, wherein:

the first device is a high voltage device.

11. The device of claim 9, wherein:

the first device is formed in a high voltage region of the
substrate.

12. The device of claim 9, wherein:

the first device is a high voltage lateral diffused transistor.

13. The device of claim 9, wherein:

the first gate dielectric layer is a high voltage gate dielectric
layer formed of oxide.

14. The device of claim 9, wherein:

the first gate electrode layer is formed of polysilicon.

15. An apparatus comprising:

a first isolation region in a substrate, wherein a top surface
of the first isolation region is lower than a top surface of
the substrate;

a gate dielectric layer over the first isolation region; and

a gate electrode layer over the gate dielectric layer,
wherein:

a first portion of the gate electrode layer is vertically
aligned with the first isolation region; and

a second portion of the gate electrode layer is formed
over the substrate, and wherein a bottom surface of the
first portion is lower than a bottom surface of the
second portion.

16. The apparatus of claim 15, further comprising:

a plurality of high voltage wells in a high voltage region of
the substrate.

17. The apparatus of claim 16, further comprising:

a first source region of a transistor in the high voltage wells;
and

a first drain region the transistor in the high voltage wells,
wherein the source region and the drain region are on
opposing sides of the first isolation region.

18. The apparatus of claim 17, wherein:

the transistor is a lateral diffused transistor.

19. The apparatus of claim 15, wherein:

the first isolation region is a shallow trench isolation (STI)
region.

20. The apparatus of claim 19, wherein:

the first isolation region is a reduced surface field (RE-
SURF) STI region.

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